

RJK5013DPP

Silicon N Channel MOS FET High Speed Power Switching

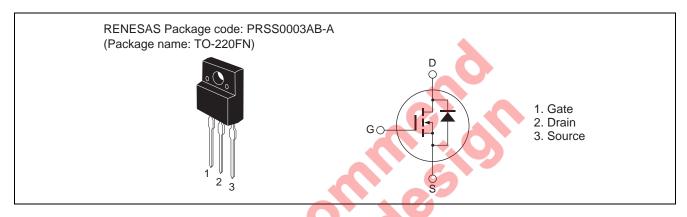
R07DS0192EJ0200 (Previous: REJ03G1585-0100) Rev.2.00

Nov 02, 2010

Features

- Low on-resistance $R_{DS(on)}=0.385~\Omega~typ.~(at~I_D=7~A,~V_{GS}=10~V,~Ta=25~^{\circ}C)$
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

		(1u-23C)		
Item	Symbol	Ratings	Unit	
Drain to source voltage	V _{DSS}	500	V	
Gate to source voltage	V _{GSS}	±30	V	
Drain current	I _D Note4	14	А	
Drain peak current	I _{D (pulse)} Note1	42	А	
Body-drain diode reverse drain current	I _{DR}	14	А	
Body-drain diode reverse drain peak current	I _{DR (pulse)} Note1	42	А	
Avalanche current	I _{AP} Note3	4	А	
Avalanche energy	E _{AR} Note3	0.88	mJ	
Channel dissipation	Pch Note2	30	W	
Channel to case thermal impedance	θch-c	4.17	°C/W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Notes: 1. PW \leq 10 $\mu s,$ duty cycle \leq 1%

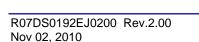
- 2. Value at Tc = 25°C
- 3. STch = 25° C, Tch $\leq 150^{\circ}$ C
- 4. Limited by maximum safe operation area

Electrical Characteristics

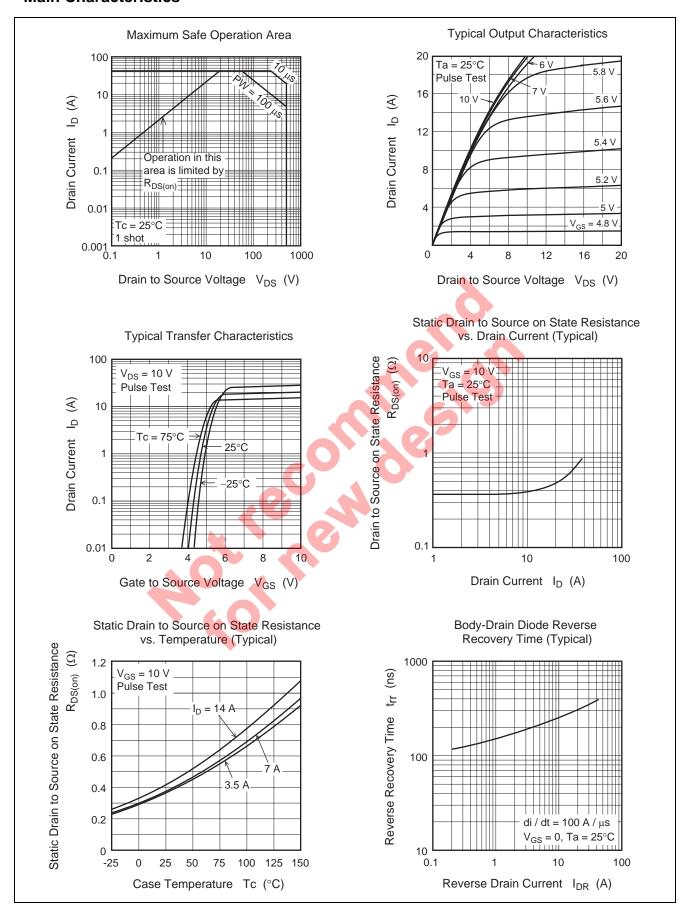
 $(Ta = 25^{\circ}C)$

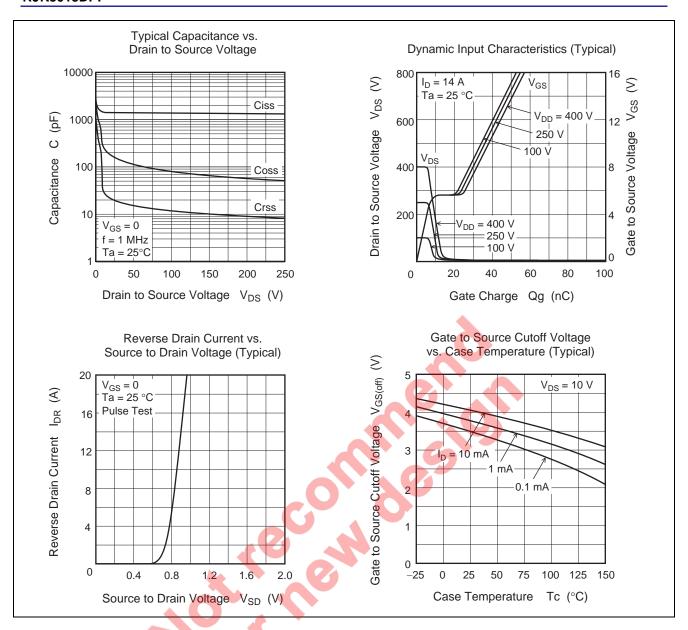
Prain to source breakdown voltage Zero gate voltage drain current Gate to source leak current Gate to source cutoff voltage Static drain to source on state esistance Input capacitance Reverse transfer capacitance Curn-on delay time Curn-off delay time Fall time Total gate charge Gate to source charge	$\begin{array}{c} V_{(BR)DSS} \\ I_{DSS} \\ I_{GSS} \\ V_{GS(off)} \\ R_{DS(on)} \\ \\ Ciss \\ Coss \\ Crss \\ t_{d(on)} \\ t_r \\ t_{d(off)} \\ t_f \\ Qg \\ \end{array}$	500 — 3.0 — — — — — — — —	Typ 0.385 1450 155 19 34 24 86 16	 1 ±0.1 4.5 0.465 	V μA V Ω PF PF PF ns	$\begin{split} I_D &= 10 \text{ mA}, V_{GS} = 0 \\ V_{DS} &= 500 \text{V}, V_{GS} = 0 \\ V_{GS} &= \pm 30 \text{V}, V_{DS} = 0 \\ V_{DS} &= 10 \text{V}, I_D = 1 \text{mA} \\ I_D &= 7 \text{A}, V_{GS} = 10 \text{V} \\ V_{DS} &= 25 \text{V} \\ V_{GS} &= 0 \\ f &= 1 \text{MHz} \\ I_D &= 7 \text{A} \\ V_{GS} &= 10 \text{V} \end{split}$
Gate to source leak current Gate to source cutoff voltage Static drain to source on state esistance Input capacitance Output capacitance Reverse transfer capacitance Turn-on delay time Turn-off delay time Fall time Total gate charge	I_{GSS} $V_{GS(off)}$ $R_{DS(on)}$ $Ciss$ $Coss$ $Crss$ $t_{d(on)}$ t_r $t_{d(off)}$ t_f Qg			±0.1 4.5 0.465 — — —	μA V Ω PF PF PF ns ns	$\begin{split} &V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \\ &V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA} \\ &I_{D} = 7 \text{ A}, V_{GS} = 10 \text{ V} \\ &V_{DS} = 25 \text{ V} \\ &V_{GS} = 0 \\ &f = 1 \text{ MHz} \\ &I_{D} = 7 \text{ A} \\ &V_{GS} = 10 \text{ V} \end{split}$
State to source cutoff voltage Static drain to source on state esistance Input capacitance Output capacitance Reverse transfer capacitance Furn-on delay time Circn-off delay time Fall time Total gate charge	$V_{GS(off)}$ $R_{DS(on)}$ $Ciss$ $Coss$ $Crss$ $t_{d(on)}$ t_r $t_{d(off)}$ t_f Qg		1450 155 19 34 24 86	4.5 0.465 — — — —	V Ω pF pF pF ns	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$ $I_{D} = 7 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note5}}$ $V_{DS} = 25 \text{ V}$ $V_{GS} = 0$ $f = 1 \text{ MHz}$ $I_{D} = 7 \text{ A}$ $V_{GS} = 10 \text{ V}$
Static drain to source on state esistance esistance Dutput capacitance Reverse transfer capacitance Turn-on delay time Rise time Turn-off delay time Fall time Total gate charge	$R_{DS(on)}$ $Ciss$ $Coss$ $Crss$ $t_{d(on)}$ t_r $t_{d(off)}$ t_f Qg		1450 155 19 34 24 86	0.465 — — — —	Ω pF pF pF ns ns	$I_D = 7 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note5}}$ $V_{DS} = 25 \text{ V}$ $V_{GS} = 0$ $f = 1 \text{ MHz}$ $I_D = 7 \text{ A}$ $V_{GS} = 10 \text{ V}$
esistance Input capacitance Dutput capacitance Reverse transfer capacitance Turn-on delay time Rise time Turn-off delay time Fall time Total gate charge	Ciss Coss Crss td(on) tr td(off) tg		1450 155 19 34 24 86		pF pF pF ns	$V_{DS} = 25 \text{ V}$ $V_{GS} = 0$ $f = 1 \text{ MHz}$ $I_{D} = 7 \text{ A}$ $V_{GS} = 10 \text{ V}$
Output capacitance Reverse transfer capacitance Furn-on delay time Rise time Furn-off delay time Fall time Fotal gate charge	$ \begin{array}{c} \text{Coss} \\ \text{Crss} \\ \text{t}_{d(on)} \\ \text{t}_{r} \\ \text{t}_{d(off)} \\ \text{t}_{f} \\ \text{Qg} \end{array} $		155 19 34 24 86		pF pF ns ns	$V_{GS} = 0$ $f = 1 \text{ MHz}$ $I_{D} = 7 \text{ A}$ $V_{GS} = 10 \text{ V}$
Reverse transfer capacitance Turn-on delay time Rise time Turn-off delay time Fall time Total gate charge	$\begin{array}{c} \text{Crss} \\ t_{d(\text{on})} \\ t_r \\ t_{d(\text{off})} \\ t_f \\ \text{Qg} \end{array}$	_ 	19 34 24 86		pF ns ns	$f = 1 \text{ MHz}$ $I_D = 7 \text{ A}$ $V_{GS} = 10 \text{ V}$
Turn-on delay time Rise time Turn-off delay time Tall time Total gate charge	$\begin{array}{c} t_{d(on)} \\ t_r \\ t_{d(off)} \\ t_f \\ Qg \end{array}$	_ 	34 24 86		ns ns	I _D = 7 A V _{GS} = 10 V
Rise time Furn-off delay time Fall time Fotal gate charge	$\begin{array}{c} t_r \\ t_{\text{d(off)}} \\ t_{\text{f}} \\ \text{Qg} \end{array}$	_ 	24 86		ns	V _{GS} = 10 V
urn-off delay time Fall time Total gate charge	t _{d(off)} t _f Qg	_ _	86	_		
fall time Total gate charge	t _f Qg					D 2570
otal gate charge	Qg	_	16		ns	$R_L = 35.7 \Omega$
-	_		10	_	ns	$Rg = 10 \Omega$
Sate to source charge	_	_	38	_	nC	V _{DD} = 400 V
	Qgs	_	8		nC	V _{GS} = 10 V
Sate to drain charge	Qgd	_	17	1	nC	I _D = 14 A
Body-drain diode forward voltage	V_{DF}	_	0.9	1.5	V	I _F = 14 A, V _{GS} = 0 Note5
Body-drain diode reverse recovery time	t _{rr}	_	310		ns	$I_F = 14 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$
lotes: 5. Pulse test						

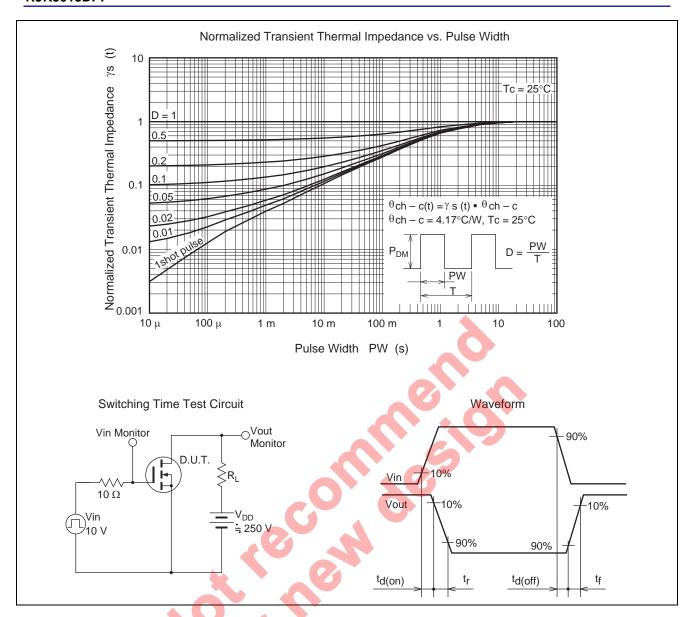
Notes: 5. Pulse test



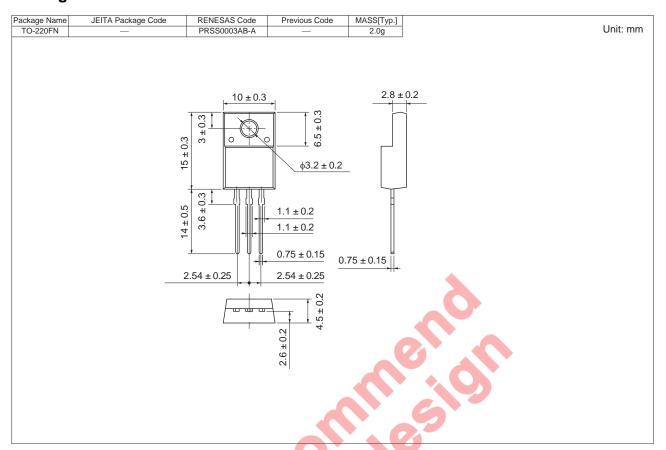
Main Characteristics







Package Dimensions



Ordering Information

Orderable Part Number	Quantity	Shipping Container
RJK5013DPP-00-T2	1050 pcs	Box (Tube)

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Renesas Electronics Canada Limited 1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada Tel: +1-905-898-5441, Fax: +1-905-898-3220

Renesas Electronics Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K
Tel: +44-1628-585-100, Fax: +44-1628-585-900

Renesas Electronics Europe GmbH Arcadiastrasse 10, 40472 Düsseldorf, Germany Tel: +49-211-65030, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd. 7th Floor, Quantum Plaza, No.27 ZhiChunLu Ha Tel: +86-10-8235-1155, Fax: +86-10-8235-7679 ı. nunLu Haidian District, Beijing 100083, P.R.China

Renesas Electronics (Shanghai) Co., Ltd.
Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

เพลายอย อเชียงเทเชง **ทยายู nong Limited** Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong Tel: +852-2866-9318, Fax: +852-2866-9022/9044

Renesas Electronics Taiwan Co., Ltd.

7F, No. 363 Fu Shing North Road Taipei, Taiwar Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

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เพราะสอน เมราะเพราะเพราะสามารถ งสท.**ษกด.** Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics Korea Co., Ltd. 11F., Samik Lavied' or Bldg., 720-2 Yeoksam-Dong, Kangnam-Ku, Seoul 135-080, Korea Tel: 482-2-588-3737, Fax: 482-2-588-5141